



#### N-CHANNEL ENHANCEMENT MODE MOSFET

## **Product Summary**

BV <sub>DSS</sub>	R <sub>DS(ON)</sub> max	I <sub>D</sub> max T <sub>C</sub> = +25°C (Note 9)
30V	$4.5 \text{m}\Omega$ @ $V_{GS} = 10V$	25A
30 V	$7.0 \text{m}\Omega$ @ $V_{GS} = 4.5 \text{V}$	25A

# **Description and Applications**

This MOSFET has been designed to minimize the on-state resistance (R<sub>DS(ON)</sub>) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

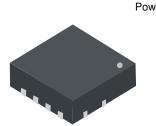
- Backlighting
- Power Management Functions
- DC-DC Converters

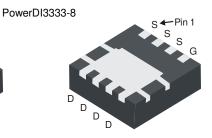
## **Features and Benefits**

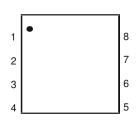
- Low R<sub>DS(ON)</sub> Ensures on State Losses Are Minimized
- Excellent Q<sub>gd x</sub> R<sub>DS(ON)</sub> Product (FOM)
- Advanced Technology for DC/DC Converters
- Small Form Factor Thermally Efficient Package Enables Higher Density End Products
- Occupies Just 33% of The Board Area Occupied by SO-8 Enabling Smaller End Product
- 100% UIS (Avalanche) Rated
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)

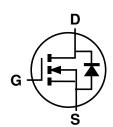
## **Mechanical Data**

- Case: PowerDI<sup>®</sup>3333-8
- Case Material: Molded Plastic, "Green" Molding Compound.
   UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections Indicator: See Diagram
- Terminals: Finish Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208
- Weight: 0.072 grams (Approximate)









Top View

**Bottom View** 

Top View

**Equivalent Circuit** 

### Ordering Information (Note 4)

Part Number	Case	Packaging
DMT3004LFG-7	PowerDI3333-8	2,000/Tape & Reel
DMT3004LFG-13	PowerDI3333-8	3,000/Tape & Reel

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/

# **Marking Information**



SG3 = Product Type Marking Code YYWW = Date Code Marking YY = Last Two Digits of Year (ex: 18 = 2018) WW = Week Code (01 to 53)



# 

Characteristic	Symbol	Value	Unit	
Drain-Source Voltage		V <sub>DSS</sub>	30	V
Gate-Source Voltage		V <sub>GSS</sub>	+20 -16	V
Continuous Drain Current (Notes 6 & 9) $V_{GS} = 10V$ $ T_C = +25^{\circ}C $ $ T_C = +70^{\circ}C $		I <sub>D</sub>	25 25	А
Continuous Drain Current (Note 5) $V_{GS} = 10V$ $T_A = +25^{\circ}C$ $T_A = +70^{\circ}C$		I <sub>D</sub>	10.4 8.3	А
Maximum Continuous Body Diode Forward Current (Note 5)	I <sub>S</sub>	3	Α	
Pulsed Drain Current (10µs pulse, Duty Cycle = 1%)	I <sub>DM</sub>	95	Α	
Avalanche Current, L=0.3mH	I <sub>AS</sub>	27	Α	
Avalanche Energy, L=0.3mH	E <sub>AS</sub>	110	mJ	

# Thermal Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 6)	$T_C = +25^{\circ}C$	$P_{D}$	42	W
Thermal Resistance, Junction to Case (Note 6)		$R_{ heta JC}$	3	°C/W
Total Power Dissipation (Note 5)	$T_A = +25^{\circ}C$	P <sub>D</sub>	2.1	W
Thermal Resistance, Junction to Ambient (Note 5)		$R_{ heta JA}$	60	°C/W
Operating and Storage Temperature Range		T <sub>J,</sub> T <sub>STG</sub>	-55 to +150	°C

# **Electrical Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 7)							
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	30	-	-	V	$V_{GS} = 0V, I_D = 250\mu A$	
Zero Gate Voltage Drain Current	I <sub>DSS</sub>		-	1	μΑ	$V_{DS} = 24V$ , $V_{GS} = 0V$	
Gate-Source Leakage	I <sub>GSS</sub>	-	-	100 -100	nA	$V_{GS} = +20V, V_{DS} = 0V$ $V_{GS} = -16V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 7)						•	
Gate Threshold Voltage	V <sub>GS(TH)</sub>	1	-	3	V	$V_{DS} = V_{GS}$ , $I_D = 250\mu A$	
Static Drain-Source On-Resistance		-	3.5	4.5	4.5 mΩ	$V_{GS} = 10V, I_D = 20A$	
Static Drain-Source On-Resistance	R <sub>DS(ON)</sub>	-	5	7.0	11177	$V_{GS} = 4.5V, I_D = 7A$	
Diode Forward Voltage	V <sub>SD</sub>	-	0.7	1	V	V <sub>GS</sub> = 0V, I <sub>S</sub> = 1A	
DYNAMIC CHARACTERISTICS (Note 8)							
Input Capacitance	Ciss		2370	-		V <sub>DS</sub> = 15V, V <sub>GS</sub> = 0V, f = 1MHz	
Output Capacitance	Coss	-	1360	-	pF		
Reverse Transfer Capacitance	C <sub>rss</sub>	-	240	-			
Gate Resistance	Rg	-	0.6	-	Ω	$V_{DS} = 0V$ , $V_{GS} = 0V$ , $f = 1MHz$	
Total Gate Charge (V <sub>GS</sub> = 4.5V)	Qg	-	20	-			
Total Gate Charge (V <sub>GS</sub> = 10V)	Qq	-	44	-	nC	V <sub>DS</sub> = 15V, I <sub>D</sub> = 20A	
Gate-Source Charge	Q <sub>gs</sub>	-	7	-	IIC		
Gate-Drain Charge	Q <sub>qd</sub>	-	8	-			
Turn-On Delay Time	t <sub>D(ON)</sub>	-	6.2	-		$V_{DD} = 15V, V_{GS} = 10V,$ $R_L = 0.75\Omega, R_G = 3\Omega, I_D = 20A$	
Turn-On Rise Time	t <sub>R</sub>	-	4.3	-			
Turn-Off Delay Time	t <sub>D(OFF)</sub>	-	21	-	ns		
Turn-Off Fall Time	t <sub>F</sub>	-	8	-			
Body Diode Reverse Recovery Time	t <sub>RR</sub>	-	25	-	ns		
Body Diode Reverse Recovery Charge	Q <sub>RR</sub>	-	37	-	nC	I <sub>F</sub> = 15A, di/dt = 500A/μs	

5.  $R_{\theta JA}$  is determined with the device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.  $R_{\theta JC}$  is guaranteed by design Notes: while R<sub>0JA</sub> is determined by the user's board design.

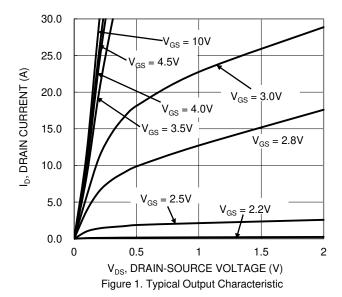
6. Thermal resistance from junction to soldering point (on the exposed drain pad).

7. Short duration pulse test used to minimize self-heating effect.

8. Guaranteed by design. Not subject to product testing.

9. Package limited.





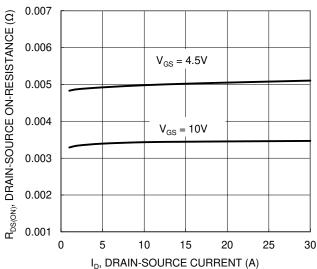


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

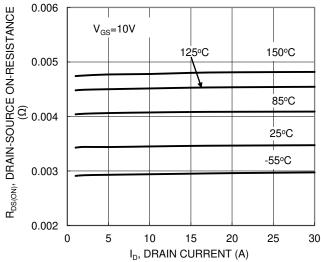
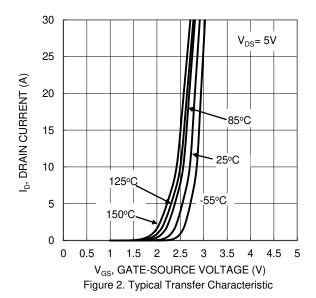


Figure 5. Typical On-Resistance vs. Drain Current and Junction Temperature



 $R_{DS(ON)}$ , DRAIN-SOURCE ON-RESISTANCE  $(\Omega)$ 0.09 0.08 0.07 0.06 0.05 0.04 0.03  $I_D = 20A$ 0.02 0.01

0.1

0

0

V<sub>GS</sub>, GATE-SOURCE VOLTAGE (V) Figure 4. Typical Transfer Characteristic

8

10

12

14

16

6

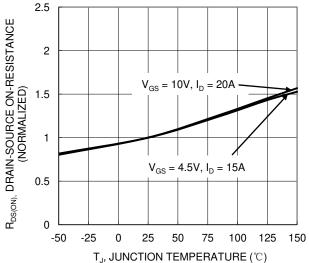


Figure 6. On-Resistance Variation with Junction Temperature



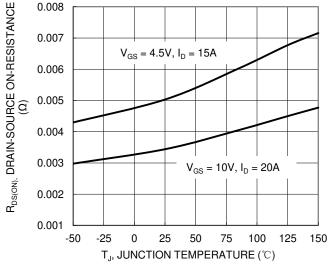
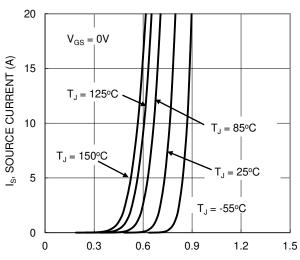


Figure 7. On-Resistance Variation with Junction Temperature



V<sub>SD</sub>, SOURCE-DRAIN VOLTAGE (V) Figure 9. Diode Forward Voltage vs. Current

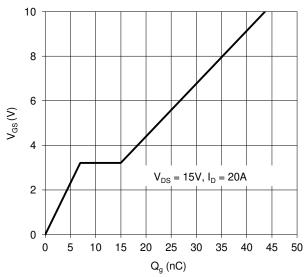


Figure 11. Gate Charge

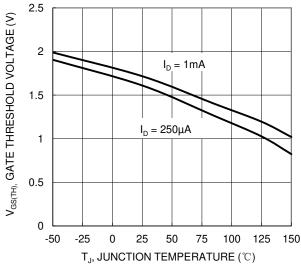
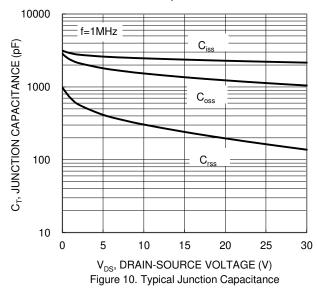


Figure 8. Gate Threshold Variation vs. Junction Temperature



1000  $R_{\text{DS(ON)}}$  Limited  $P_W = 1 ms$ 100 ID, DRAIN CURRENT (A) 10  $P_w = 10ms$ P<sub>W</sub> =100ms  $T_{J(Max)} = 150 \,^{\circ}\text{C}$ T<sub>A</sub>=25°C =10s 0.1 Single Pulse ∰ DC DUT on 1\*MRP board  $V_{GS} = 10V$ 0.01 0.01 100 V<sub>DS</sub>, DRAIN-SOURCE VOLTAGE (V) Figure 12. SOA, Safe Operation Area



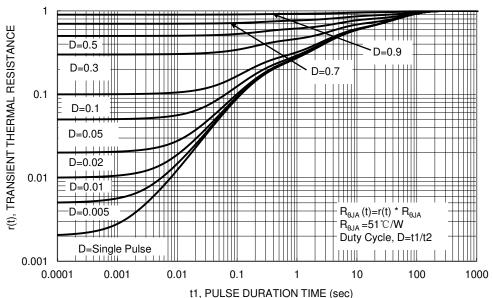


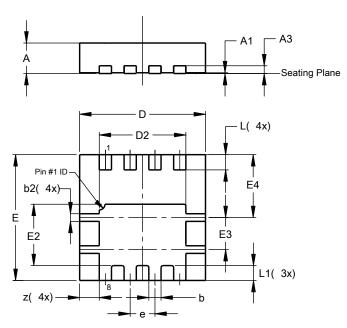
Figure 13. Transient Thermal Resistance



# **Package Outline Dimensions**

Please see http://www.diodes.com/package-outlines.html for the latest version.

### PowerDI3333-8

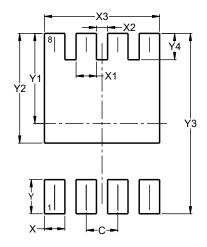


PowerDI3333-8					
Dim	Min	Max	Тур		
Α	0.75	0.85	0.80		
<b>A</b> 1	0.00	0.05	0.02		
A3	1	-	0.203		
b	0.27	0.37	0.32		
b2	0.15	0.25	0.20		
D	3.25	3.35	3.30		
D2	2.22	2.32	2.27		
E	3.25	3.35	3.30		
E2	1.56	1.66	1.61		
E3	0.79	0.89	0.84		
E4	1.60	1.70	1.65		
е	_	_	0.65		
L	0.35	0.45	0.40		
L1	_	_	0.39		
Z	_	_	0.515		
All Dimensions in mm					

# **Suggested Pad Layout**

Please see http://www.diodes.com/package-outlines.html for the latest version.

#### PowerDI3333-8



Dimensions	Value (in mm)
С	0.650
X	0.420
X1	0.420
X2	0.230
Х3	2.370
Υ	0.700
Y1	1.850
Y2	2.250
Y3	3.700
Y4	0.540



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